

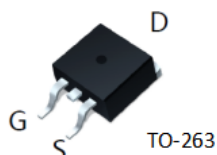


TSB830M

500V N-Channel MOSFET

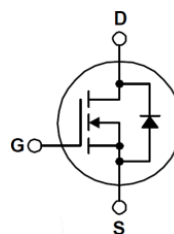
General Description

This Power MOSFET is produced using Truesemi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.



Features

- 6.0A, 500V, Max. $R_{DS(on)} = 1.3\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 29nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter		TSB830M	Units
V_{DSS}	Drain-Source Voltage		500	V
V_{GS}	Gate-Source Voltage		± 30	V
I_D	Drain Current	$T_C = 25^\circ\text{C}$	6.0	A
		$T_C = 100^\circ\text{C}$	3.8	A
I_{DM}	Pulsed Drain Current (Note 1)		18	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		285	mJ
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)		72	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	$^\circ\text{C}$

* Drain current limited by maximum junction temperature.

Thermal Resistance Characteristics

Symbol	Parameter	TSB830M	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.6	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.64	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.75\text{ A}$	--		1.3	Ω
g_{FS}	Forward Transconductance	$V_{DS}=10\text{ V}, I_D=5\text{ A}$	--	8	--	S

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1450	--	pF
C_{oss}	Output Capacitance		--	95	--	pF
C_{rss}	Reverse Transfer Capacitance		--	10	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Time	$V_{DS} = 250\text{ V}, I_D = 6.0\text{ A},$ $R_G = 25\text{ }\Omega$	--	5	--	ns
t_r	Turn-On Rise Time		--	55	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	25	--	ns
t_f	Turn-Off Fall Time		--	55	--	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 6.0\text{ A},$ $V_{GS} = 10\text{ V}$	--	13	30	nC
Q_{gs}	Gate-Source Charge		--	4	--	nC
Q_{gd}	Gate-Drain Charge		--	6	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

I _S	Continuous Source-Drain Diode Forward Current		--	--	6.0	A
I _{SM}	Pulsed Source-Drain Diode Forward Current		--	--	18	
V _{SD}	Source-Drain Diode Forward Voltage	I _S = 5.0A, V _{GS} = 0 V	--	--	1.4	V
t _{rr}	Reverse Recovery Time	I _S =6.0A, V _{GS} = 0 V di _F /dt = 100 A/μs	--	275	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.7	--	uC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=10\text{ mH}, I_{AS}=7.0\text{ A}, V_{DD}=50\text{ V}, R_G=25\text{ }\Omega$, Starting $T_J=25^{\circ}\text{C}$
3. Pulse Test: Pulse width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Characteristics

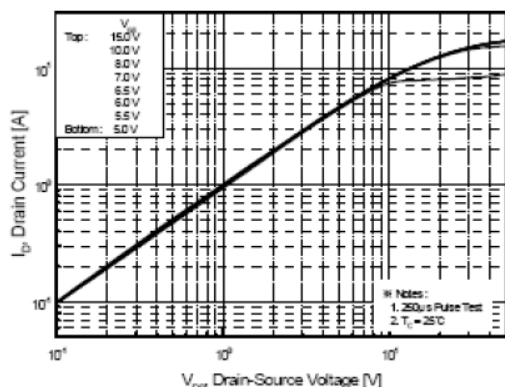


Figure 1. On-Region Characteristics

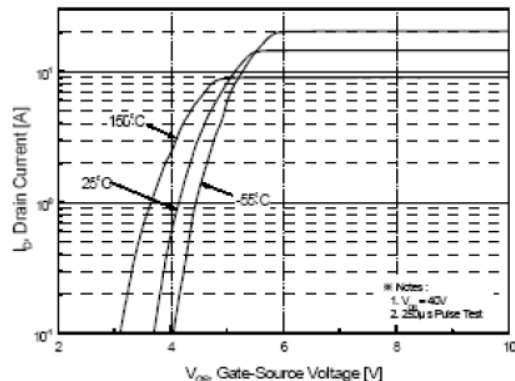


Figure 2. Transfer Characteristics

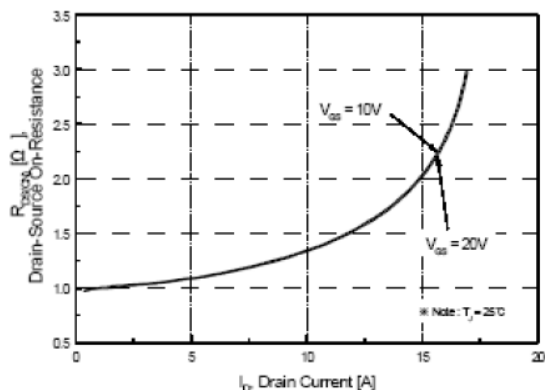


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

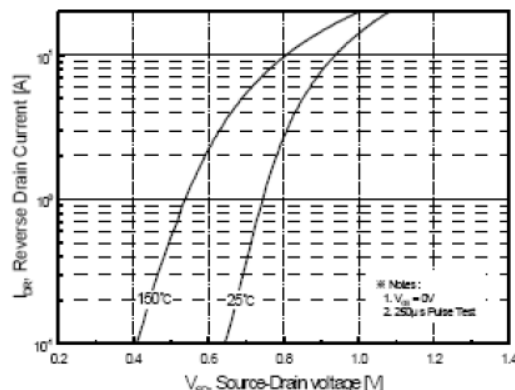


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

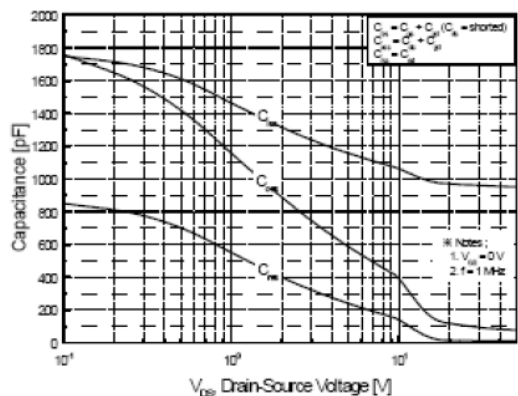


Figure 5. Capacitance Characteristics

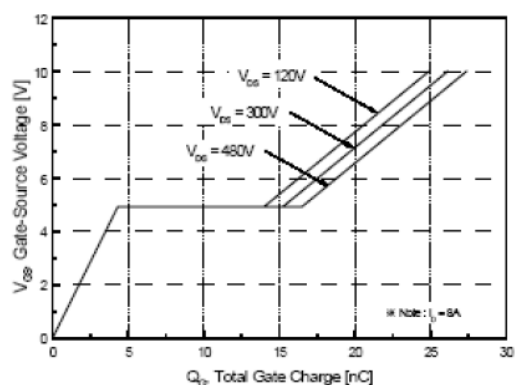


Figure 6. Gate Charge Characteristics

Typical Characteristics

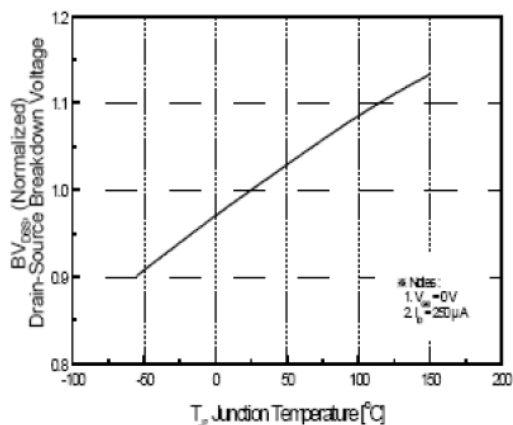


Figure 7. Breakdown Voltage Variation vs Temperature

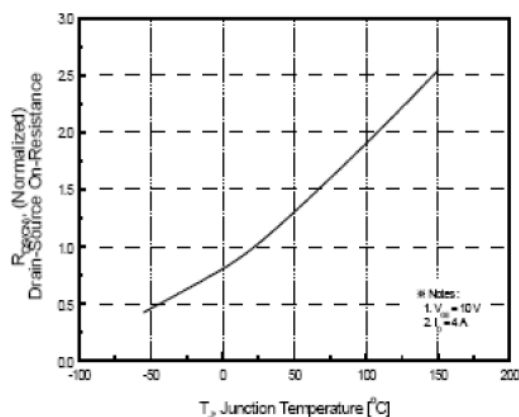


Figure 8. On-Resistance Variation vs Temperature

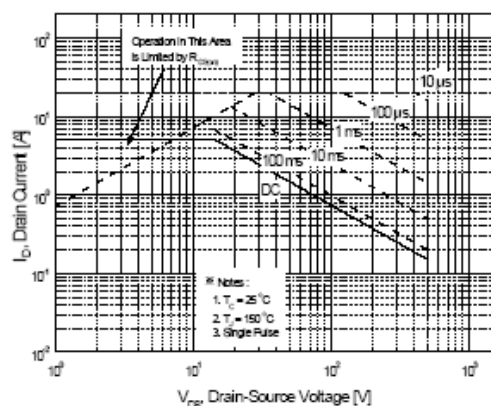


Figure 9-1. Maximum Safe Operating Area for TSB830M

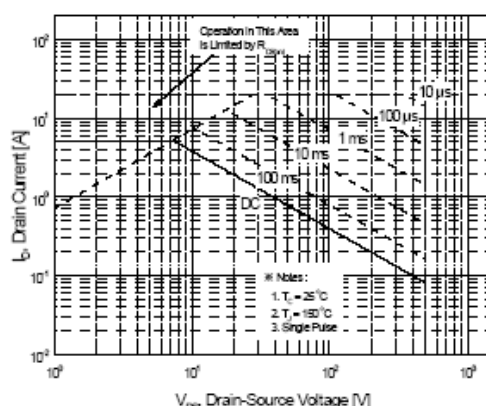


Figure 9-2. Maximum Safe Operating Area for TSF830M

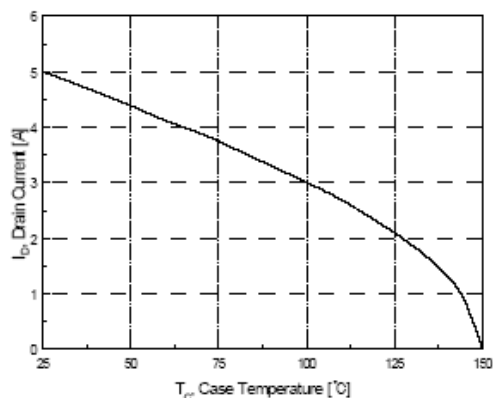


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics

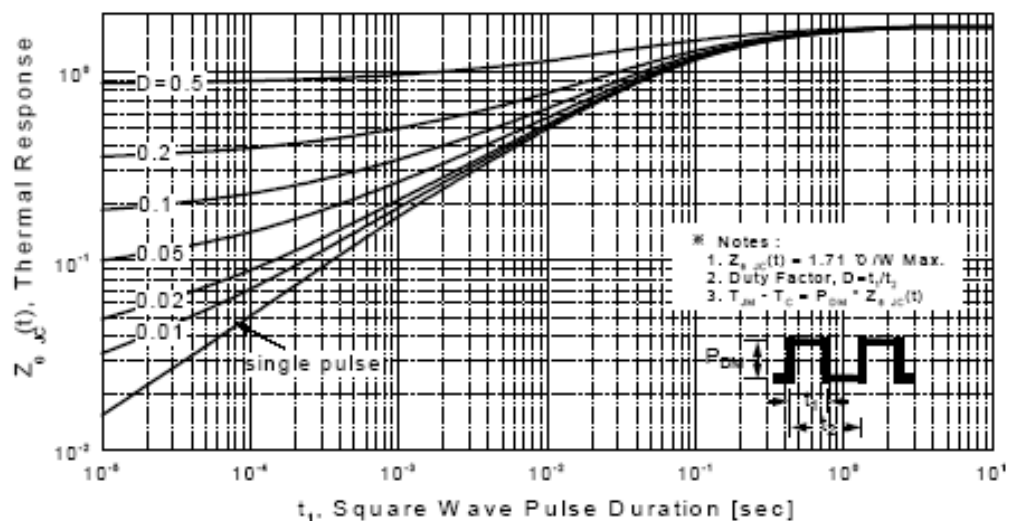


Figure 11-1. Transient Thermal Response Curve
for TSB830M

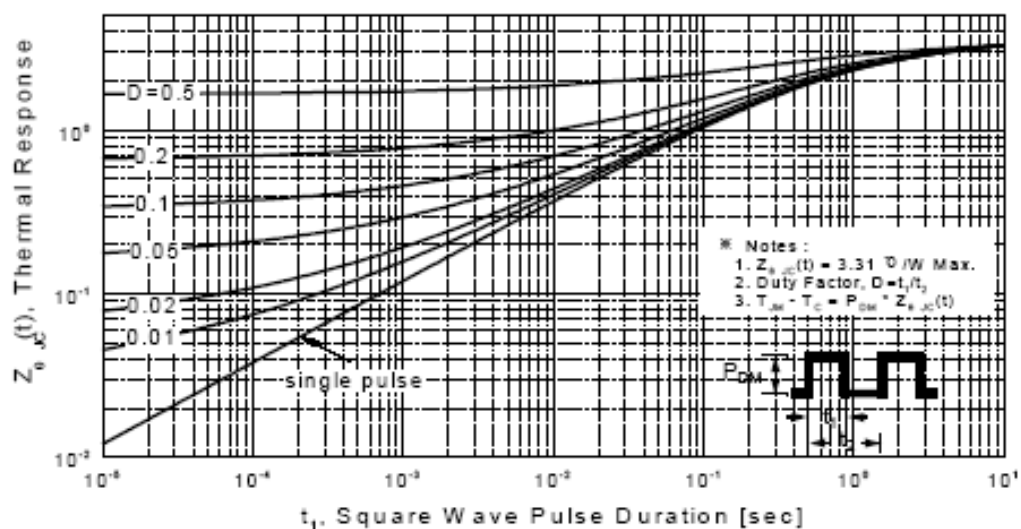


Figure 11-2. Transient Thermal Response Curve
for TSF830M

Fig 12. Gate Charge Test Circuit & Waveform

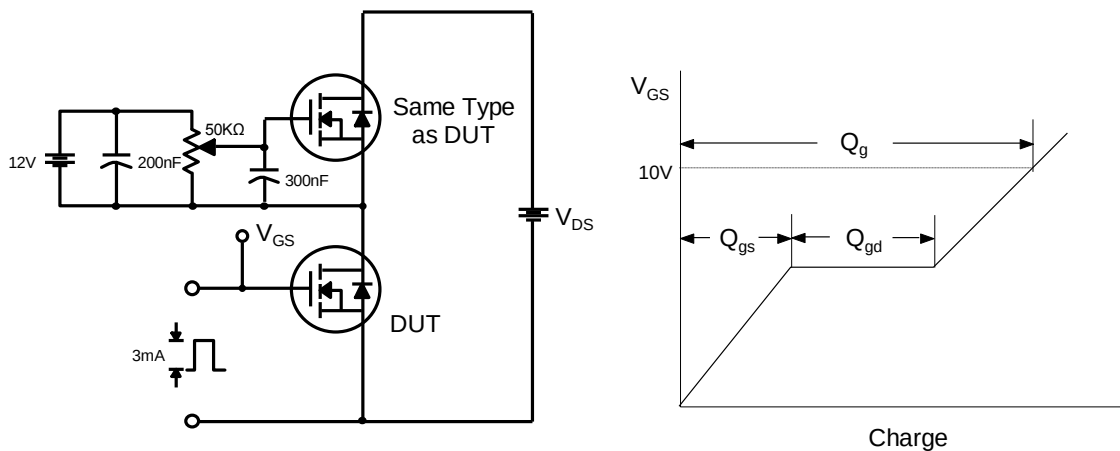


Fig 13. Resistive Switching Test Circuit & Waveforms

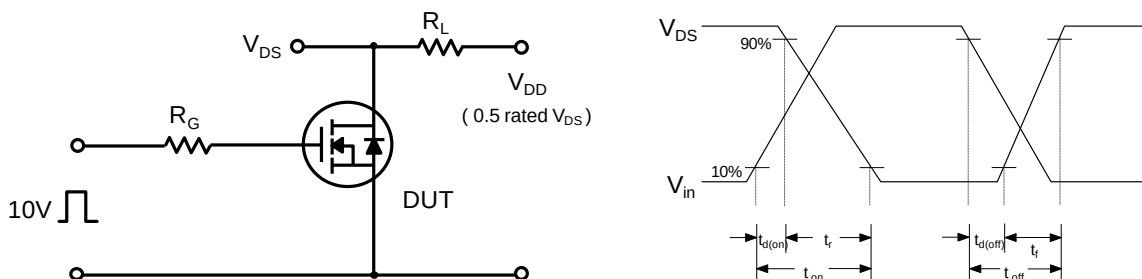


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

